

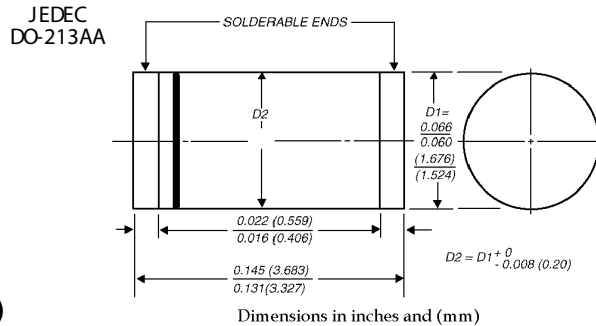
Mechanical Dimension

SD103AMM~CMM

Description



GLASS MINIMELF(DO-213AA)



FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance

Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	SD103AMM	SD103BMM	SD103CMM	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}				
Working Peak DC Blocking Voltage	V _{RWM}	40	30	20	V
RMS Reverse Voltage	V _{R(RMS)}	28	21	14	V
Forward Continuous Current	I _{FM}	350			mA
Repetitive Peak Forward Current @t≤1.0s	I _{FRM}	1.0			A
Power Dissipation	P _d	400			mW
Thermal Resistance Junction to Ambient	R _{θJA}	250			°C/W
Storage temperature	T _{STG}	-65~+175			°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	40			V	IR=10μA
SD103AMM		40				IR=10μA
SD103BMM		30				IR=10μA
SD103CMM		20				IR=10μA
Forward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	I _{RM}			5.0	μA	V _R =30V V _R =20V V _R =10V
Capacitance between terminals	C _T		50		pF	V _R =0V,f=1.0MHz
Reverse Recovery Time	t _{rr}		10		ns	I _F =I _R =50~200mA I _{rr} =0.1I _R ,R _L =100Ω

Typical Characteristics SD103AMM-SD103CMM

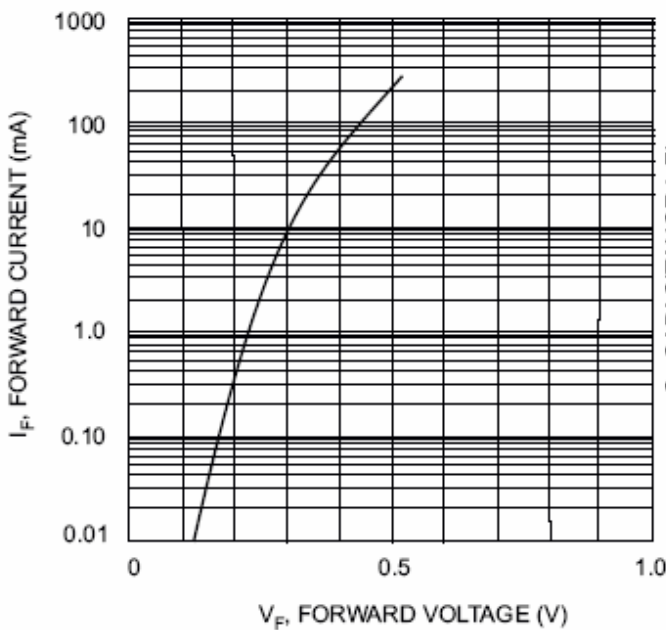


Fig. 1 Typical Forward Characteristics

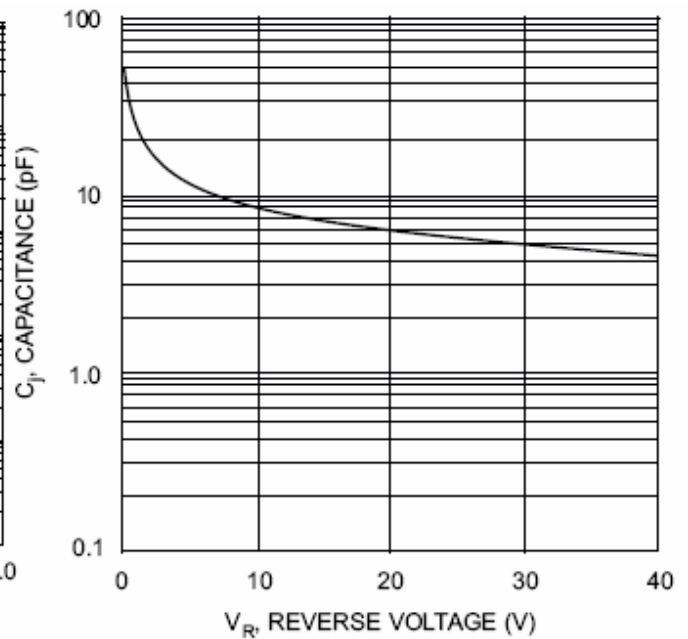


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

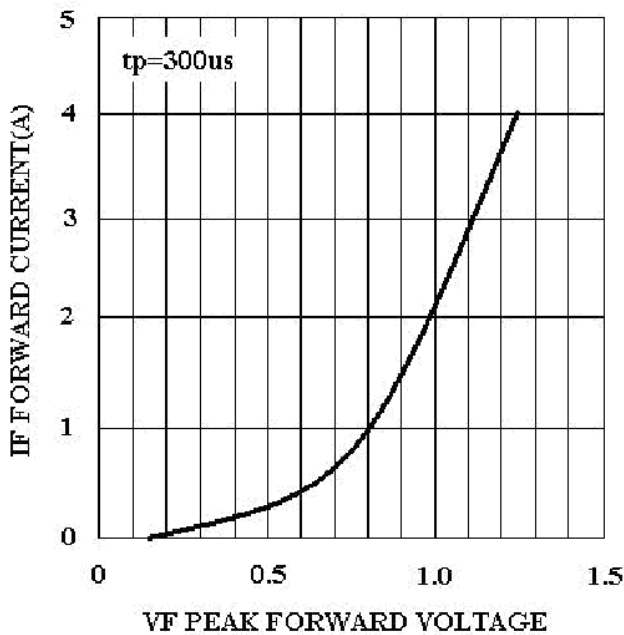


Fig. 3 TYPICAL HIGH CURRENT FORWARD

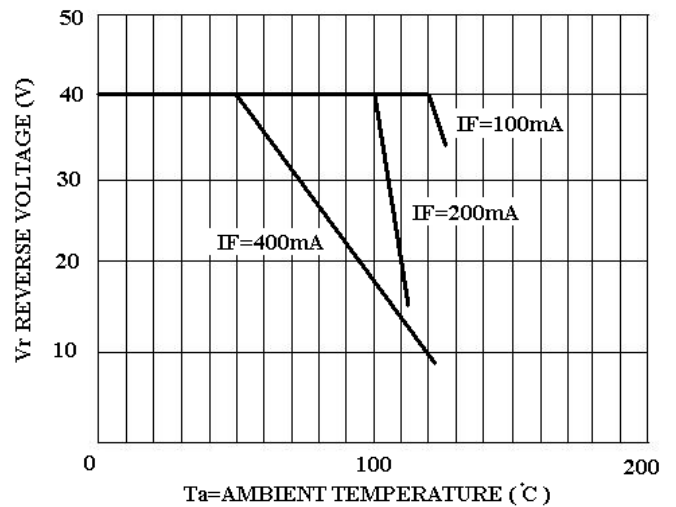


Fig 4 BLOCKING VOLTAGE DERATING CURVES